

Features

- LOW OFFSET VOLTAGE: 10 μV (Max)
- ZERO DRIFT: 0.008 μV/°C
- 0.1Hz to 10Hz Noise: 1.1 μV_{PP}
- Low Supply Current: 42 μA per Amplifier
- Bandwidth: 350 kHz
- Slew Rate: 0.16 V/µs
- High Gain, 130 dB High CMRR and PSRR
- Rail-to-rail Input and Output Swing
- –40°C to 125°C Operation Range
- Small Packages: SC70 and SOT23 (TP5531)

Applications

- Transducer Amplifier
- Bidirectional Current Sense
- DC Offset Correction
- Temperature Measurement
- Remote Located Sensors
- Battery-Powered Instruments
- Electronic Weigh Scales

1.8V, 42µA, RRIO, Zero Drift Op-amps Description

The 3PEAK TP5531/2/4 low-power chopper stabilized operational amplifiers provide input offset voltage correction for very low offset and offset drift over time and temperature. The devices operate with a single supply voltage as low as 1.8V, while drawing 42µA per amplifier of quiescent current with a gain bandwidth product of 350kHz. They are unity gain stable, have no 1/f noise, have good Power Supply Rejection Ratio (PSRR) and Common Mode Rejection Ratio (CMRR), and feature rail-to-rail input and output swing.

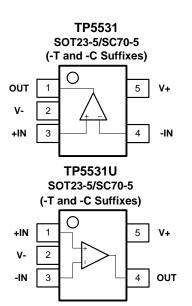
The devices were designed using an advanced CMOS process. The TP5531 (single version) is available in SC70-5, SOT23-5 and SO-8 packages. The TP5532 (dual version) is offered in MSOP-8 and SO-8 package. The TP5534 (quad version) is available in TSSOP-14 and SOIC-14 package. All versions are specified for operation from -40°C to 125°C.

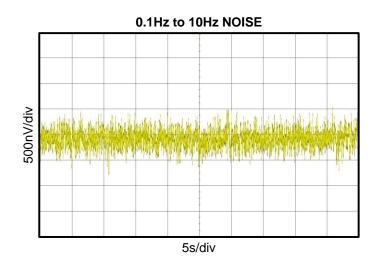
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Related Zero-Drift Op-amps

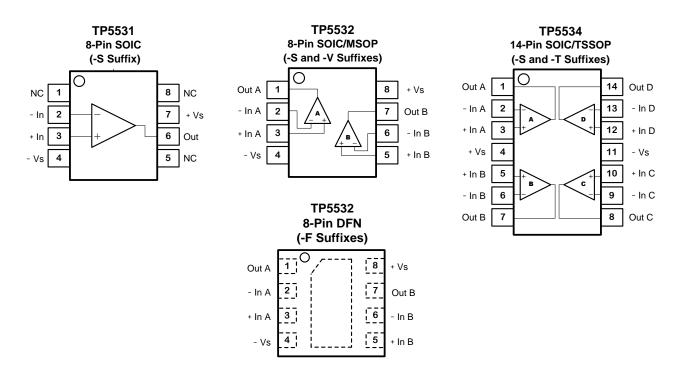
V _{os} (Max.)	10 µV	5 µV
GBWP	350 kHz	3.5 MHz
Supply Current	42 µA	500 µA
e _N at 1 kHz	55 nV/√Hz	15 nV/√Hz
Single	TP5531	TP5551
Dual	TP5532	TP5552
Quad	TP5534	TP5554

Pin Configuration (Top View)





Pin Configuration (Top View, continued)



The thermal pad of DFN package is recommended to be float or connected to -Vs

Order Information

Model Name	Order Number	Package	Transport Media, Quantity	Marking Information
TP5531	TP5531-TR	SOT23-5	Tape and Reel, 3,000	E31T
TP5531U	TP5531U-TR	SOT23-5	Tape and Reel, 3,000	E31U
11 33310	TP5531U-CR	SC70-5	Tape and Reel, 3,000	31V
	TP5532-SR	SOIC-8	Tape and Reel, 4,000	TP5532
TP5532	TP5532-FR	DFN-8 2*2	Tape and Reel, 3,000	532
	TP5532-VR	MSOP-8	Tape and Reel, 3,000	TP5532
TP5534	TP5534-SR	SOIC-14	Tape and Reel, 2,500	TP5534
11 0004	TP5534-TR	TSSOP-14	Tape and Reel, 3,000	TP5534

Absolute Maximum Ratings Note 1

Supply Voltage:	6V
Input Voltage:	.V ⁻ − 0.2 to V ⁺ + 0.2
Input Current: +IN, -IN Note 2	±20mA
Output Short-Circuit Duration Not	^{te 3} Indefinite
Current at Supply Pins	±50mA

Note 1: Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. Exposure to any Absolute Maximum Rating condition for extended periods may affect device reliability and lifetime.

2

Note 2: The inputs are protected by ESD protection diodes to each power supply. If the input extends more than 500mV beyond the power supply, the input current should be limited to less than 10mA.

Note 3: A heat sink may be required to keep the junction temperature below the absolute maximum. This depends on the power supply voltage and how many amplifiers are shorted. Thermal resistance varies with the amount of PC board metal connected to the package. The specified values are for short traces connected to the leads.

ESD, Electrostatic Discharge Protection

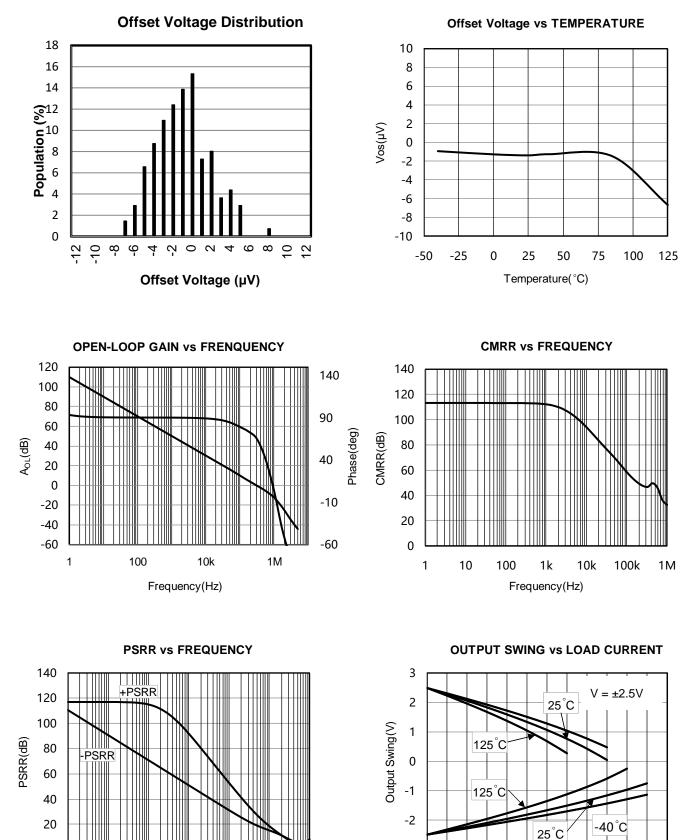
Symbol	Parameter	Condition	Minimum Level	Unit
HBM	Human Body Model ESD	ANSI/ESDA/JEDEC JS-001	7	kV
CDM	Charged Device Model ESD	ANSI/ESDA/JEDEC JS-002	2	kV

Electrical Characteristics

At $T_A = 27^{\circ}$ C, $V_S = 5$ V, $R_L = 10$ k Ω , $V_{CM} = V_{DD}/2$, unless otherwise noted.

SYMBO L	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNITS
Vs	Supply Voltage Range		1.8		5.5	V
_		TP5531		45	65	μA
la	Quiescent current per amplifier	TP5532/TP5534		42	60	μA
		V _{CM} = 2.5V	-10	1	10	μV
Vos	Input Offset Voltage	V _{CM} = 0.05 to 4.95V	-20		20	μV
		V _S = 1.8V, V _{CM} = 0.9V	-20		20	μV
dV _{OS} /dT	vs temperature			0.008	0.05	μV/°C
PSRR	vs power supply	Vs = 3V to 5V	100	120		dB
M	input voltage noise, f=0.01Hz to 1Hz			0.4		μV _{pp}
Vn	input voltage noise, f=0.1Hz to 10Hz			1.1		μV _{pp}
en	Input voltage noise density, f=1kHz			55		nV/√Hz
C	Input capacitor, Differential			3		pF
CIN	Input capacitor, Common-Mode			2		pF
1	Input Bias Current			±50		pА
B	Over temperature			±800		pА
los	Input offset current			±100		pА
Vсм	Common-mode voltage range		(V-) - 0.1		(V ₊)+0.1	V
CMRR	Common-mode rejection ratio	V _{CM} =0.5 to 4.5V	100	120	, ,	dB
Vo	Output Voltage Swing from rail	R∟=10kΩ		10	25	mV
lsc	Short-circuit current			±60		mA
GBWP	Unity Gain Bandwidth	C _L =100pF		350		kHz
SR	Slew rate	G=+1, CL=100pF		0.16		V/µs
tor	Overload recovery time	G=-10		60		μs
ts	Settling time to 0.01%	C _L =100Pf, G=+1, 5V Step		40		μs
Avol	Open-Loop Voltage Gain	$(V-)+100mV < V_0 < (V+)-100mV,$ R _L = 100kΩ	100	120		dB
		SC70-5 (SOT353)		250		
		SOT23-5		200		
0	Thermal Resistance Junction to	MSOP-8		210		00/14/
θја	Ambient	SOIC-8		158		°C/W
		SOIC-14		83		
		TSSOP-14		100		

1.8V, 42µA, RRIO, Zero Drift Op-amps **Typical Performance Characteristics**



-3

0

10

100

1k

Frequency(Hz)

10k

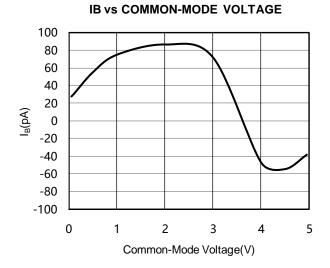
100k

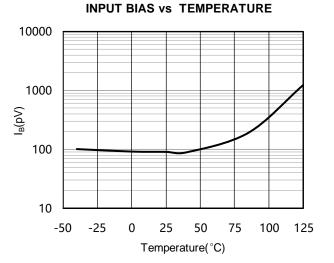
1M

0

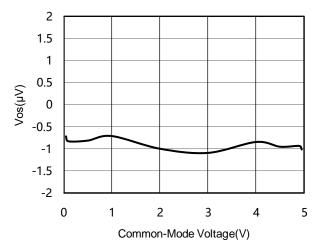
1

Typical Performance Characteristics(continue)



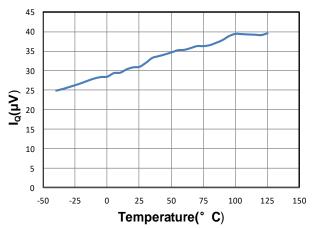


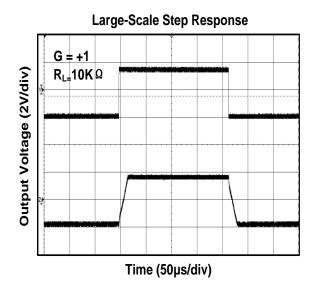
Vosvs COMMON-MODE VOLTAGE



Quiescent Current Distribution 160 140 120 POPULATION 100 80 60 40 20 0 35.75 35.75 36.5 37.25 38.75 38.75 39.5 28.25 29.75 29.75 30.5 31.25 32.75 33.5 33.5 41 41.75 42.5 44.75 27.5 13.25 44 **Ιq (μA**)

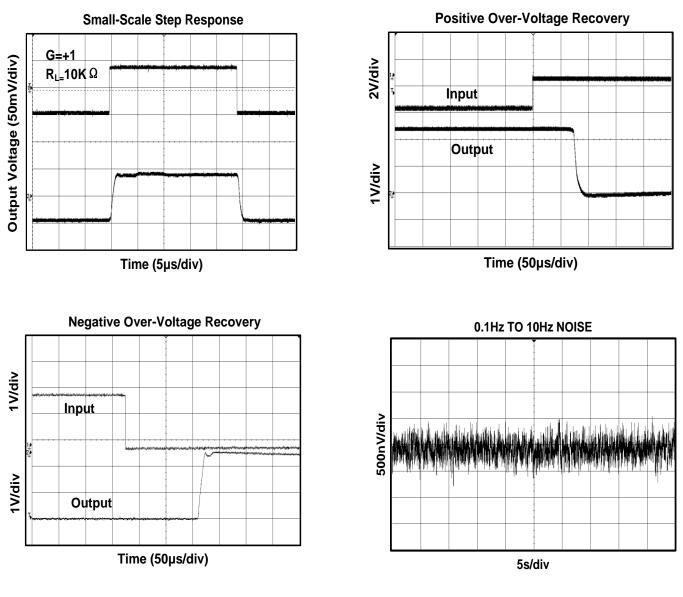
QUIESCENT CURRENT vs TEMPERATURE

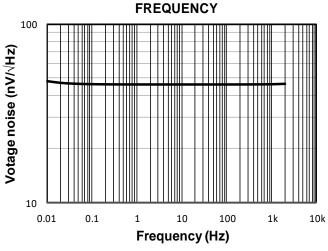




1.8V, 42µA, RRIO, Zero Drift Op-amps

Typical Performance Characteristics(continue)

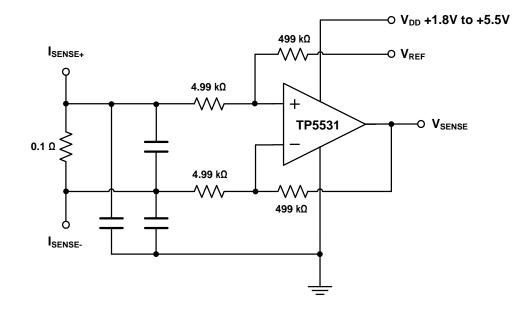




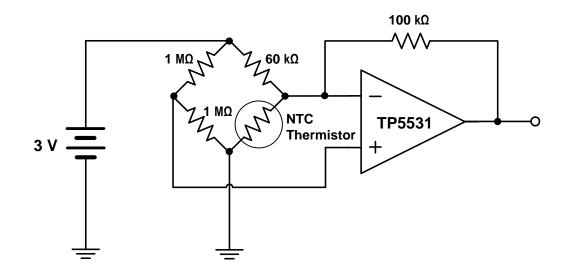
VOLTAGE NOISE SPECTRAL DENSITY vs FREQUENCY

Typical Applications

Bi-Directional Current Sense Amplifier



Thermistor Measurement



1.8V, 42µA, RRIO, Zero Drift Op-amps **Pin Functions**

-IN: Inverting Input of the Amplifier.

+IN: Non-Inverting Input of Amplifier.

OUT: Amplifier Output. The voltage range extends to within mV of each supply rail.

V+ or +V_s: Positive Power Supply. Typically the voltage is from 1.8V to 5.5V. Split supplies are possible as long as the voltage between V+ and V– is between 1.8V and 5.5V. A bypass capacitor of 0.1μ F as close to the part as

possible should be used between power supply pins or between supply pins and ground.

V- or -V_s: Negative Power Supply. It is normally tied to ground. It can also be tied to a voltage other than ground as long as the voltage between V⁺ and V⁻ is from 1.8V to 5.5V. If it is not connected to ground, bypass it with a capacitor of 0.1μ F as close to the part as possible.

Operation

The TP553x series op amps are zero drift, rail-to-rail operation amplifiers that can be run from a single-supply voltage. They use an auto-calibration technique with a time-continuous 350 kHz op amp in the signal path while consuming only 42 μ A of supply current per channel. This amplifier is zero-corrected with an 120 kHz clock. Upon power-up, the amplifier requires approximately 100 μ s to achieve specified V_{os} accuracy. This design has no aliasing or flicker noise.

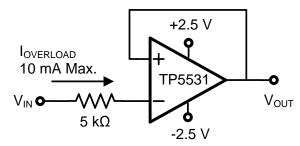
Applications Information

Rail-To-Rail Input And Output

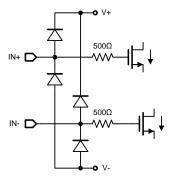
The TP553x series op amps feature rail-to-rail input and output with a supply voltage from 1.8V to 5.5 V. This allows the amplifier inputs to have a wide common mode range (50mV beyond supply rails) while maintaining high CMRR (130dB) and maximizes the signal to noise ratio of the amplifier by having the V_{OH} and V_{OL} levels be at the V+ and V-rails, respectively.

Input Protection

The TP553x series op amps have internal ESD protection diodes that are connect between the inputs and supply rail. When either input exceeds one of the supply rails by more than 300mV, the ESD diodes become forward biased and large amounts of current begin to flow through them. Without current limiting, this excessive fault current causes permanent damage to the device. Thus an external series resistor must be used to ensure the input currents never exceed 10mA.



Current-limiting resistor required if input voltage exceeds supply rails by >0.5V.



INPUT ESD DIODE CURRENT LIMITING-UNITY GAIN

Low Input Referred Noise

Flicker noise, as known as 1/f noise, is inherent in semiconductor devices and increases as frequency decreases. So at lower frequencies, flicker noise dominates, causing higher degrees of error for sub-Hertz frequencies or dc precision application.

The TP553x series amplifiers are chopper stabilized amplifiers, the flicker noise is reduced greatly because of this technique. This reduction in 1/f noise allows the TP553x to have much lower noise at dc and low frequency compared to standard low noise amplifier.

Residual Voltage Ripple

The chopping technique can be used in amplifier design due to the internal notch filter. Although the chopping related voltage ripple is suppressed, higher noise spectrum exists at the chopping frequency and its harmonics due to residual ripple.

So if the frequency of input signal is nearby the chopping frequency, the signal maybe interfered by the residue ripple. To further suppress the noise at the chopping frequency, it is recommended that a post filter be placed at the output of the amplifier.

Broad Band and External Resistor Noise Considerations

The total broadband noise output from any amplifier is primarily a function of three types of noise: input voltage noise from the amplifier, input current noise from the amplifier, and thermal (Johnson) noise from the external resistors used around the amplifier. These noise sources are not correlated with each other and their combined noise can be summed in a root sum squared manner. The full equation is given as:

$$e_n total = [e_n^2 + 4kTR_s + (i_n \times R_s)^2]^{1/2}$$

Where:

 e_n = the input voltage noise density of the amplifier.

 i_n = the input current noise of the amplifier.

 $R_{\rm S}$ = source resistance connected to the noninverting terminal.

k= Boltzmann' s constant (1.38x10⁻²³J/K). *T*= ambient temperature in Kelvin (K).

The total equivalent rms noise over a specific bandwidth is expressed as:

$$e_{n,rms} = e_n total \times \sqrt{BW}$$

The input voltage noise density (en) of the TP553x is 55 nV/ \sqrt{Hz} , and the input current noise can be neglected. When the source resistance is 190 k Ω , the voltage noise contribution from the source resistor and the amplifier are equal. With source resistance greater than 190 k Ω , the overall noise of the system is dominated by the Johnson noise of the resistor itself.

High Source Impedance Application

The TP553x series op amps use switches at the chopper amplifier input, the input signal is chopped at 125 kHz to reduce input offset voltage down to 10μ V. The dynamic behavior of these switches induces a charge injection current to the input terminals of the amplifier. The charge injection current has a DC path to ground through the resistances seen at the input terminals of the amplifier. Higher input impedance causes an apparent shift in the input bias current of the amplifier.

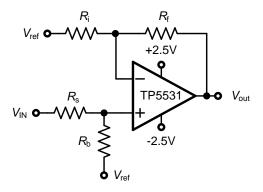
Because the chopper amplifier has charge injection currents at each terminal, the input offset current will be larger than standard amplifiers. The Ios of TP553x are 150pA under the typical condition. So the input impedance should be

1.8V, 42µA, RRIO, Zero Drift Op-amps

balanced across each input. The input impedance of the amplifier should be matched between the IN+ and IN- terminals to minimize total input offset current. Input offset currents show up as an additional output offset voltage, as shown in the following equation:

$$v_{os,total} = v_{os} - R_f \times I_{os}$$

For a gain configure using $1M\Omega$ feedback resistor, a 150pA total input offset current will have an additional output offset voltage of 0.15mV. By keeping the input impedance low and balanced across the amplifier inputs, the input offset current effect will be suppressed efficiently.



Circuit Implication for reducing Input offset current effect

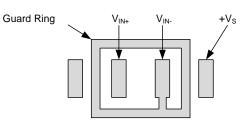
PCB Surface Leakage

In applications where low input bias current is critical, Printed Circuit Board (PCB) surface leakage effects need to be considered. Surface leakage is caused by humidity, dust or other contamination on the board. It is recommended to use multi-layer PCB layout and route the OPA's -IN and +IN signal under the PCB surface.

The effective way to reduce surface leakage is to use a guard ring around sensitive pins (or traces). The guard ring is biased at the same voltage as the sensitive pin. An example of this type of layout is shown in Figure 2 for Inverting Gain application.

1. For Non-Inverting Gain and Unity-Gain Buffer:

- a) Connect the non-inverting pin (V_{IN} +) to the input with a wire that does not touch the PCB surface.
- b) Connect the guard ring to the inverting input pin (VIN-). This biases the guard ring to the Common Mode input voltage.
- 2. For Inverting Gain and Trans-impedance Gain Amplifiers (convert current to voltage, such as photo detectors):
 - a) Connect the guard ring to the non-inverting input pin (V_{IN} +). This biases the guard ring to the same reference voltage as the op-amp (e.g., $V_{DD}/2$ or ground).
 - b) Connect the inverting pin (V_{IN} -) to the input with a wire that does not touch the PCB surface.

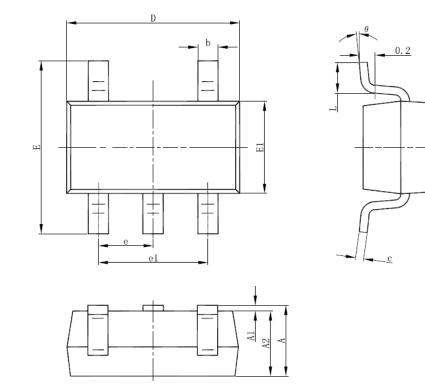


The Layout of Guard Ring

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Package Outline Dimensions

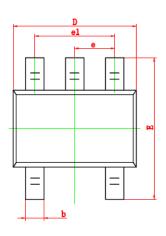
SOT23-5

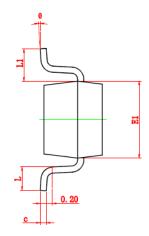


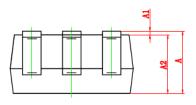
Sumb a l	Dimensions Ir	n Millimeters	Dimensions	s In Inches
Symbol	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
С	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
е	0.950	(BSC)	0.037	(BSC)
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

1.8V, 42µA, RRIO, Zero Drift Op-amps Package Outline Dimensions

SC-70-5 (SOT353)





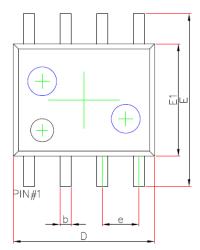


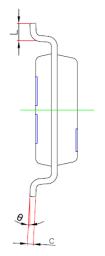
Symbol	Dimensions	Dimensions In Millimeters		s In Inches
Symbol	Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.150	0.350	0.006	0.014
С	0.110	0.175	0.004	0.007
D	2.000	2.200	0.079	0.087
E	2.150	2.450	0.085	0.096
E1	1.150	1.350	0.045	0.053
е	0.650 TYP.		0.026	TYP.
e1	1.200	1.400	0.047	0.055
L	0.260	0.460	0.010	0.018
L1	0.525	0.525 REF. 0.021 REF.		REF.
θ	0°	8°	0°	8°

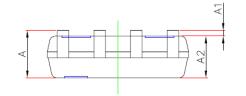
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Package Outline Dimensions

SOP-8 (SOIC-8)





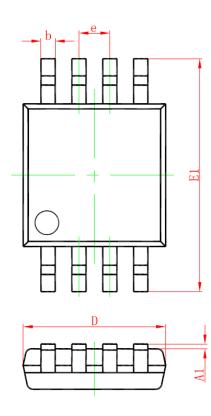


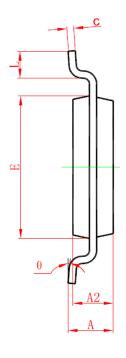
Symbol	Dimensions Ir	n Millimeters	Dimension	s In Inches
Symbol	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
С	0.170	0.250	0.007	0.010
D	4.700	5.100	0.185	0.201
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
е	1.270(1	BSC)	0.050(BSC)	
Ĺ	0.400	0.800	0.016	0.031
θ	0°	8°	0°	8°

1.8V, 42µA, RRIO, Zero Drift Op-amps

Package Outline Dimensions

MSOP-8

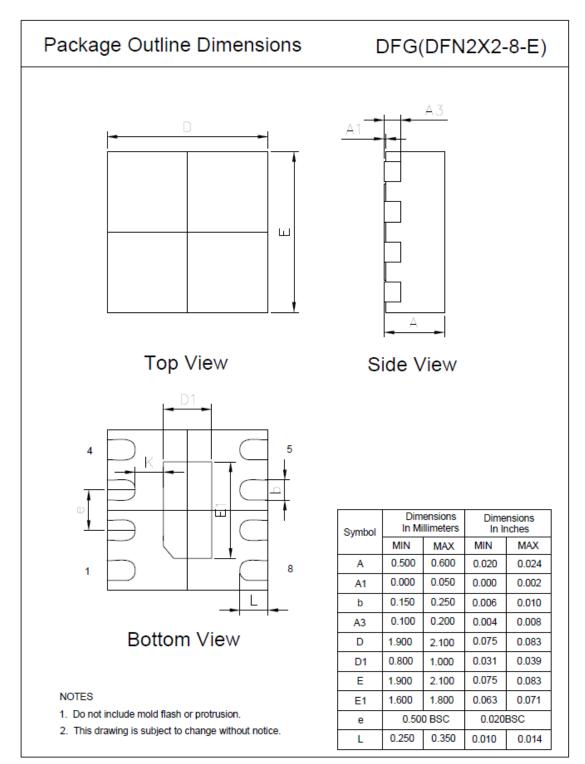




Sumb a l	Dimensions Ir	n Millimeters	Dimensions	In Inches
Symbol	Min	Max	Min	Max
Α	0.820	1.100	0.032	0.043
A1	0.020	0. 150	0.001	0.006
A2	0.750	0.950	0.030	0.037
b	0.250	0. 380	0.010	0.015
С	0.090	0. 230	0.004	0.009
D	2.900	3. 100	0.114	0. 122
е	0.650	(BSC)	0.026	(BSC)
E	2.900	3. 100	0.114	0. 122
E1	4. 750	5.050	0. 187	0. 199
L	0.400	0.800	0.016	0. 031
θ	0°	6°	0°	6°

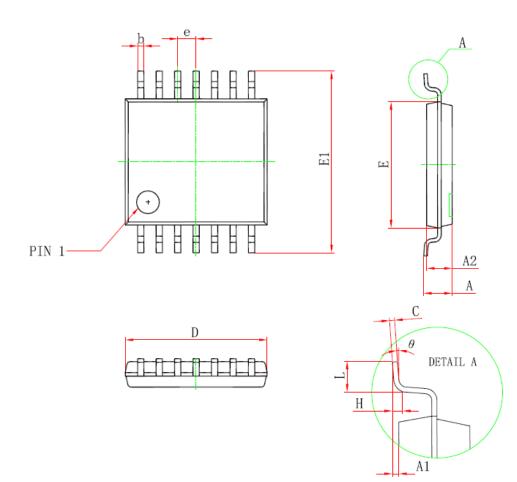
Package Outline Dimensions

DFN-8 2*2



Package Outline Dimensions

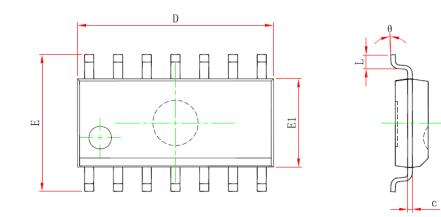
TSSOP-14

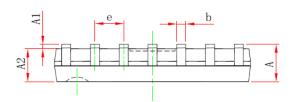


C	Dimensions In Millimeters		Dimension	s In Inches
Symbo1	Min	Max	Min	Max
D	4.900	5.100	0.193	0.201
Е	4.300	4.500	0.169	0.177
b	0.190	0.300	0.007	0.012
с	0.090	0.200	0.004	0.008
E1	6.250	6.550	0.246	0.258
А		1.200		0.047
A2	0.800	1.000	0.031	0.039
A1	0.050	0.150	0.002	0.006
e	0.65 (BSC)		0.026(BSC)	
L	0.500	0.700	0.020	0.028
Н	0.25(T	YP)	0.01(TYP)
θ	1°	7°	1 °	7°

Package Outline Dimensions

SOP-14 (SOIC-14)





Symbol	Dimensions In Millimeters		Dimensions In	Inches
	Min	Max	Min	Max
А	——	1.750		0.069
A1	0.100	0.250	0.004	0.010
A2	1.250		0.049	
b	0.310	0.510	0.012	0.020
С	0.100	0.250	0.004	0.010
D	8.450	8.850	0.333	0.348
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
e	1.270	(BSC)	0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0 °	8°	0°	8°

1.8V, 42µA, RRIO, Zero Drift Op-amps **Revision History**

Revision	Notes
B.1	Update package outline dimensions of DFN-8 2*2.
	Delete part number which is not in manufacture: TP5531-CR, TP5531-SR